

ABSTRACT

The present invention relates to high purity hafnium having a purity of 4N or higher excluding zirconium and gas components and an oxygen content of 40wtppm or less, and a target and thin film formed from such high purity hafnium, and high purity hafnium having a purity of 4N or higher excluding zirconium and gas components and in which the content of sulfur and phosphorus is respectively 10wtppm or less. The present invention also relates to a high purity hafnium material which uses a hafnium sponge with reduced zirconium as the raw material, and in which the content of oxygen, sulfur and phosphorus containing in the hafnium is reduced, as well as to a target and thin film formed from such material, and to the manufacturing method of high purity hafnium. Thereby provided is efficient and stable manufacturing technology which enables the manufacture of a high purity hafnium material, and a target and thin film formed from such material.